# MSKSEMI















**ESD** 

TVS

TSS

MOV

**GDT** 

**PLED** 

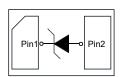
# Brodnet data speet

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#### **DFN1610-2L**



Circuit diagram

## **Descriptions**

The ESD56201DXX-MS is a transient voltage suppressor designed to protect power interfaces. It is suitable to replace multiple discrete components in portable electronics.

The ESD56201DXX-MS is specifically designed to protect power lines.

The ESD56201DXX-MS is available in DFN1610-2L package. Standard products are Pb-free and Halogen-free.

#### **Features**

- Reverse stand-off voltage: 4.85V ~ 24V
- Surge protection according to IEC61000-4-5 see Table 4
- ESD protection according to IEC61000-4-2 ±30kV (contact and air discharge)
- Low clamping voltage
- Solid-state silicon technology

## **Applications**

- Power supply protection
- Power management

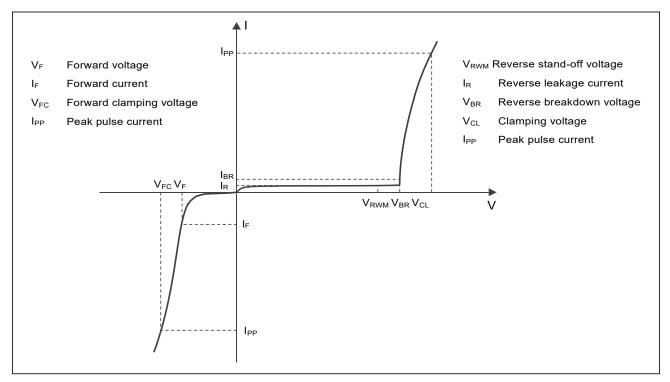
#### **Order information**

| Device         | Package    | Shipping       | Marking |
|----------------|------------|----------------|---------|
| ESD56201D04-MS | DFN1610-2L | 3000/Tape&Reel | D4*     |
| ESD56201D05-MS | DFN1610-2L | 3000/Tape&Reel | l*      |
| ESD56201D10-MS | DFN1610-2L | 3000/Tape&Reel | J*      |
| ESD56201D12-MS | DFN1610-2L | 3000/Tape&Reel | K*      |
| ESD56201D15-MS | DFN1610-2L | 3000/Tape&Reel | L*      |
| ESD56201D18-MS | DFN1610-2L | 3000/Tape&Reel | S*      |
| ESD56201D20-MS | DFN1610-2L | 3000/Tape&Reel | N*      |



| Parameter                                       | Symbol           | Rating  | Unit |  |
|---|------------------|---------|------|--|
| Peak pulse power (tp = 8/20µs)                  | P <sub>pk</sub>  | 1800    | W    |  |
| ESD according to IEC61000-4-2 air discharge     |                  | ±30     | kV   |  |
| ESD according to IEC61000-4-2 contact discharge | V <sub>ESD</sub> | ±30     |      |  |
| Junction temperature                            | TJ               | 125     | °C   |  |
| Operating temperature                           | T <sub>OP</sub>  | -40~85  | °C   |  |
| Lead temperature                                | TL               | 260     | °C   |  |
| Storage temperature                             | T <sub>STG</sub> | -55~150 | °C   |  |

## Electrical characteristics (T<sub>A</sub> = 25°C, unless otherwise noted)



**Definitions of electrical characteristics** 

## Electrical characteristics (T<sub>A</sub> = 25°C, unless otherwise noted)

| P/N            | Reverse<br>Stand-off<br>Voltage<br>V <sub>RWM</sub> (V) | Breakdown voltage<br>V <sub>BR</sub> (V) I <sub>BR</sub> =<br>1mA |      | Reverse<br>leakage<br>current I <sub>RM</sub> (µA)<br>at V <sub>RWM</sub> |          | Forward voltage<br>V <sub>F</sub> (V) I <sub>F</sub> = 20mA |      | Junction<br>capacitance<br>F = 1MHz,<br>VR=0V (pF) |      |      |
|----------------|---|---|------|---|----------|---|------|--|------|------|
|                | Max   | Min   | Тур  | Max   | Typ<br>e | Max   | Min  | Max  | Тур  | Max  |
| ESD56201D04-MS | 4.85  | 5.2   | 5.7  | 6.2   | -        | 5.0   | 0.45 | 1.25   | 1100 | 1300 |
| ESD56201D05-MS | 5.0   | 6.6   | 7.1  | 7.6   | -        | 2.0   | 0.45 | 1.25   | 1050 | 1250 |
| ESD56201D10-MS | 10.0  | 10.7  | 11.3 | 12.3  | -        | 0.1   | 0.45 | 1.25   | 545  | 650  |
| ESD56201D12-MS | 12.0  | 12.7  | 13.7 | 14.6  | -        | 0.1   | 0.45 | 1.25   | 425  | 510  |
| ESD56201D15-MS | 15.0  | 16.0  | 17.5 | 19.0  | -        | 0.1   | 0.45 | 1.25   | 325  | 350  |
| ESD56201D18-MS | 18.0  | 19.2  | 21.1 | 23.0  | -        | 0.1   | 0.45 | 1.25   | 270  | 300  |
| ESD56201D20-MS | 20.0  | 21.4  | 23.2 | 25.0  | -        | 0.1   | 0.45 | 1.25   | 250  | 275  |

|                | Rated peak pulse current lpp (A) 1)2) | Clamping voltage V <sub>CL</sub> (V) at I <sub>PP</sub> (A) <sup>1)2)</sup> |      |  |
|----------------|---------------------------------------|---|------|--|
| P/N            | Max.                                  | Тур.  | Max. |  |
| ESD56201D04-MS | 120                                   | 10.5  | 12.0 |  |
| ESD56201D05-MS | 100                                   | 11.0  | 13.0 |  |
| ESD56201D10-MS | 86                                    | 17.5  | 20.0 |  |
| ESD56201D12-MS | 75                                    | 19.5  | 22.0 |  |
| ESD56201D15-MS | 60                                    | 27.0  | 30.0 |  |
| ESD56201D18-MS | 50                                    | 32.0  | 35.0 |  |
| ESD56201D20-MS | 45                                    | 35.0  | 38.0 |  |

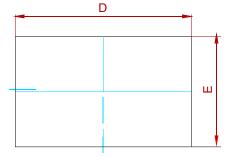
#### Notes:

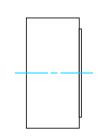
- 1 Non-repetitive current pulse, according to IEC61000-4-5. (8/20µs current waveform)
- 2 Non-repetitive current pulse, according to IEC61000-4-2.
- 3 Measured from pin 1 to pin 2.

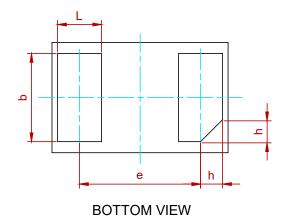
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### **PACKAGE MECHANICAL DATA**





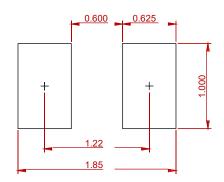


TOP VIEW

SIDE VIEW

| Cumbal | Di   | Dimensions in Millimeters |      |  |  |
|--------|------|---------------------------|------|--|--|
| Symbol | Min. | Тур.                      | Max. |  |  |
| А      | 0.45 | 0.50                      | 0.55 |  |  |
| A1     | 0.00 | 0.02                      | 0.05 |  |  |
| С      |      | 0.15 Ref.                 |      |  |  |
| b      | 0.75 | 0.80                      | 0.85 |  |  |
| L      | 0.35 | 0.40                      | 0.45 |  |  |
| D      | 1.55 | 1.60                      | 1.65 |  |  |
| Е      | 0.95 | 1.00                      | 1.05 |  |  |
| е      |      | 1.10 BSC                  |      |  |  |
| h      |      | 0.20 Ref.                 |      |  |  |

### Recommend PCB Layout (Unit: mm)



#### Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

## **REEL SPECIFICATION**

| P/N            | PKG        | QTY  |
|----------------|------------|------|
| ESD56201DXX-MS | DFN1610-2L | 3000 |



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